

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6056	((front or top or first) near2 (side or surface)) and ((back or bottom or second) near2 (side or surface)) and (substrate or semiconductor or wafer) and metal\$4 and (clean\$4 or etch\$4 or rins\$4)).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:41
L2	148	((front or top or first) near2 (side or surface)) and ((back or bottom or second) near2 (side or surface)) and (substrate or semiconductor or wafer) and metal\$4 and (clean\$4 or etch\$4 or rins\$4) and acid and copper).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:35
L3	491	((front or top or first) near2 (side or surface)) and ((back or bottom or second) near2 (side or surface)) and (substrate or semiconductor or wafer) and metal\$4 and (clean\$4 or etch\$4 or rins\$4) and acid).clm.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:36
L4	873	1 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:36
L5	14	2 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:36
L6	79	3 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:37
L7	56	1 and "134"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:37
L8	7	7 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:37
L9	369	1 and "216"/\$.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:37
L11	122	9 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 15:20
L12	116705	((front or top or first) near2 (side or surface)) and ((back or bottom or second) near2 (side or surface)) and (substrate or semiconductor or wafer) and metal\$4 and (clean\$4 or etch\$4 or rins\$4))	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 14:41

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L13	117814	((front or top or first) near2 (side or surface)) and ((back or bottom or second) near2 (side or surface)) and (substrate or semiconductor or wafer) and metal\$4 and (clean\$4 or etch\$4 or rins\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:41
L14	5386	((front or top or first) near2 (side or surface)) same ((back or bottom or second) near2 (side or surface)) same (substrate or semiconductor or wafer) same (metal\$4 or copper) same (clean\$4 or etch\$4 or rins\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:42
L15	1122	((front or top or first) near2 (side or surface)) with ((back or bottom or second) near2 (side or surface)) with (substrate or semiconductor or wafer) with (metal\$4 or copper) with (clean\$4 or etch\$4 or rins\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:44
L16	185	15 and @py<"1998"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:43
L17	19	((front or top or first) near2 (side or surface)) with (water or H2O or "H. sub.20") and ((back or bottom or second) near2 (side or surface)) with (HCl or (hydrochloric near2 acid))) and (substrate or semiconductor or wafer) and (metal\$4 or copper) and (clean\$4 or etch\$4 or rins\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:56
L18	6	((front or top or first) near2 (side or surface)) with (water or H2O or "H. sub.20") and ((back or bottom or second) near2 (side or surface)) with (HCl or (hydrochloric near2 acid))) with (spin\$4 or rotat\$4) and (substrate or semiconductor or wafer) and (metal\$4 or copper) and (clean\$4 or etch\$4 or rins\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 14:58
L19	0	((front or top or first) near2 (side or surface)) with (water or H2O or "H. sub.20") same ((back or bottom or second) near2 (side or surface)) with (HCl or (hydrochloric near2 acid))) same (spin\$4 or rotat\$4) same (substrate or semiconductor or wafer) same (metal\$4 or copper) same (clean\$4 or etch\$4 or rins\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:00

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L20	4	(((((front or top or first) near2 (side or surface)) with (water or H2O or "H.sub.2O")) same (((back or bottom or second) near2 (side or surface)) with (HCl or (hydrochloric near2 acid)))) same (spin\$4 or rotat\$4) same (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:03
L21	0	(((((front or top or first) near1 (side or surface)) near5 (water or H2O or "H.sub.2O")) same (((back or bottom or second) near1 (side or surface)) near5 (HCl or (hydrochloric near2 acid)))) same (spin\$4 or rotat\$4) same (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:15
L22	155	(substrate or semiconductor or wafer) same (clean\$4 or etch\$4 or rins\$4) same (spin\$4 or rotat\$4) same ((water or H2O or "H.sub.2O") and (HCl or (hydrochloric near2 acid))) same (metal\$4 or copper\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:25
L23	64	22 and @py<"1998"	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/01 15:21
L24	39	((substrate or semiconductor or wafer) with (clean\$4 or etch\$4 or rins\$4) with (spin\$4 or rotat\$4)) same ((water or H2O or "H.sub.2O") same (HCl or (hydrochloric near2 acid))) same (metal\$4 or copper\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:27
L25	44	((substrate or semiconductor or wafer) with (clean\$4 or etch\$4 or rins\$4) with (spin\$4 or rotat\$4)) same ((nitrogen or N2 or "N.sub.2") same (HF or (hydrofluoric near2 acid))) same (metal\$4 or copper\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2007/12/01 15:27